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Evolution of orientation degree, lattice dynamics and electronic band structure properties in nanocrystalline ianthanum-doped bismuth titanate ferroelectric films by chemical solution deposition

<u>Jinzhong Zhang</u>,^a <u>Xiangui Chen</u>,^a <u>Kai Jiang</u>,^a <u>Yude Shen</u>,^a <u>Yawei Li</u>,^a <u>Zhigao Hu</u>*^a and <u>Junhao Chu</u>^a Show Affiliations *Dalton Trans.*, 2011, **40**, 7967-7975

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